L	Hits	Search Text	DB	Time stamp
Number 1	2619850	(chip die dice semiconductor ic	USPAT;	2004/10/15
	2013030	(integrated adj circuit))	US-PGPUB; EPO; JPO;	15:58
2	885496	control and memory	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/15 15:58
3	42532	<pre>(stack stacked stacking stackable multilevel) with ((chip die dice semiconductor ic (integrated adj circuit)) )</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/15 16:00
4	1435264	lead leadframe (lead adj frame)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/10/15 16:00
5	3135	(control and memory) and ((stack stacked stacking stackable multilevel) with ((chip die dice semiconductor ic (integrated adj circuit)) )) and (lead leadframe (lead adj frame))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/15 16:00
6	502306		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/15 16:03
7	1251	<pre>((control and memory) and ((stack stacked stacking stackable multilevel) with ((chip die dice semiconductor ic (integrated adj circuit)) )) and (lead leadframe (lead adj frame))) and ((bond pad terminal electrode) with (both different))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/15 16:01
8	743		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/15 16:02
9	592278	(bond pad terminal electrode wire) with (both different)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/10/15 16:04
10	1251	<pre>((bond pad terminal electrode wire) with (both different)) and (((control and memory) and ((stack stacked stacking stackable multilevel) with ((chip die dice semiconductor ic (integrated adj circuit)) )) and (lead leadframe (lead adj frame))) and ((bond pad terminal electrode) with (both different)))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/15 16:03
11	287099	(bond pad terminal electrode) and wire and "13"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/15 16:04

12	743	(bond pad terminal electrode) and wire	USPAT;	2004/10/15
		and (((bond pad terminal electrode wire)	US-PGPUB;	16:05
		with (both different)) and (((control and	EPO; JPO;	
		memory) and ((stack stacked stacking	DERWENT;	
		stackable multilevel) with ((chip die	IBM TDB	
		dice semiconductor ic (integrated adj	_	
		circuit)) )) and (lead leadframe (lead		
		adj frame))) and ((bond pad terminal		
		electrode) with (both different))))		

L	Hits	Search Text	DB	Time stamp
Number		·		
1	2619850	(chip die dice semiconductor ic	USPAT;	2004/10/15
		(integrated adj circuit))	US-PGPUB;	15:58
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	885496	control and memory	USPAT;	2004/10/15
			US-PGPUB;	15:58
			EPO; JPO;	
			DERWENT;	
_			IBM_TDB	
3	42532		USPAT;	2004/10/15
		multilevel) with ((chip die dice	US-PGPUB;	16:00
		semiconductor ic (integrated adj	EPO; JPO;	
		circuit)) )	DERWENT;	
4	1435364	1	IBM_TDB	2004/10/15
4	1435264	lead leadframe (lead adj frame)	USPAT;	2004/10/15
			US-PGPUB; EPO; JPO;	18.00
			DERWENT;	
			IBM TDB	
5	3135	(control and memory) and ((stack stacked	USPAT;	2004/10/15
5	3133	stacking stackable multilevel) with	US-PGPUB;	16:00
		((chip die dice semiconductor ic	EPO; JPO;	10.00
		(integrated adj circuit)))) and (lead	DERWENT;	
		leadframe (lead adj frame))	IBM TDB	
6	502306		USPAT;	2004/10/15
•		different)	US-PGPUB;	16:01
		,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
7	1251	((control and memory) and ((stack stacked	USPAT;	2004/10/15
		stacking stackable multilevel) with	US-PGPUB;	16:01
		((chip die dice semiconductor ic	EPO; JPO;	
		(integrated adj circuit)) )) and (lead	DERWENT;	
		leadframe (lead adj frame))) and ((bond	IBM_TDB	
		pad terminal electrode) with (both		
		different))		1
8	743	1 2 /	USPAT;	2004/10/15
		((stack stacked stacking stackable	US-PGPUB;	16:02
		multilevel) with ((chip die dice	EPO; JPO;	
		semiconductor ic (integrated adj	DERWENT;	
		circuit)))) and (lead leadframe (lead	IBM_TDB	
		adj frame))) and ((bond pad terminal		
	1	electrode) with (both different)))		1